Ordering number : ENA0189A



SANYO Semiconductors DATA SHEET

FSS218-

N-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- · Motor drive applications.
- · Inverter drive applications.
- · 4V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		35	V
Gate-to-Source Voltage	VGSS	30 A 7 E 2 E	±20	V
Drain Current (DC)	ID	_ sil G\//d = -	8	Α
Drain Current (PW≤10s)	ID	Duty cycle≤1%	8.5	А
Drain Current (PW≤10μs)	IDP	Duty cycle≤1%	32	А
Allowable Power Dissipation	PD	Mounted on a ceramic board (2000mm²X0.8mm), PW≤10s	1.8	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	110	Ratings		
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	35	11 W W		V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =35V, V _{GS} =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	VGS(off)	VDS=10V, ID=1mA	1.5		2.5	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =8A	5.4	9		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =8A, V _{GS} =10V		20	26	mΩ
	RDS(on)2	ID=4A, VGS=4V		38	54	mΩ
Input Capacitance	Ciss	V _{DS} =10V, f=1MHz		1050		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		200		pF
Reverse Transfer Capacitance	Crss	V _{DS} =10V, f=1MHz		140		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.	444	17		ns
Rise Time	tr	See specified Test Circuit.		65	Lac	ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		75	Dr.	ns
Fall Time	tf	See specified Test Circuit.		45		ns

Marking: S218 Continued on next page.

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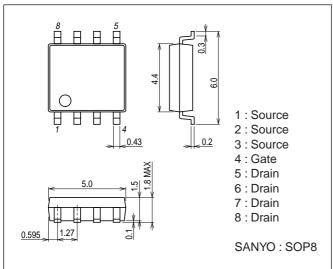
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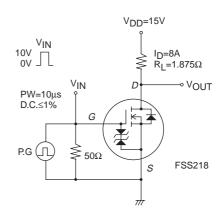
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =10V, I _D =8A		19		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =10V, I _D =8A		3.3		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =10V, V _{GS} =10V, I _D =8A		3.5		nC
Diode Forward Voltage	V _{SD}	IS=8A, VGS=0V		0.85	1.2	V

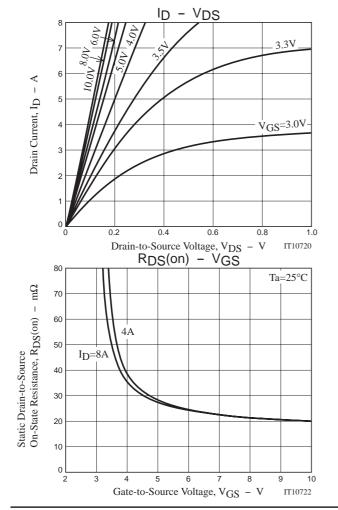
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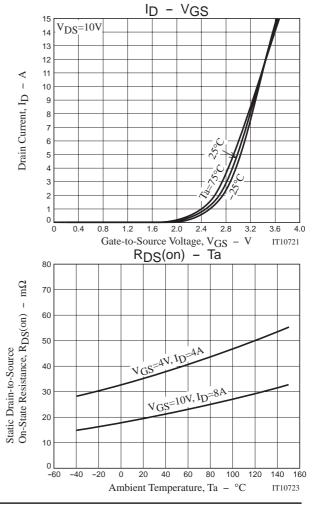
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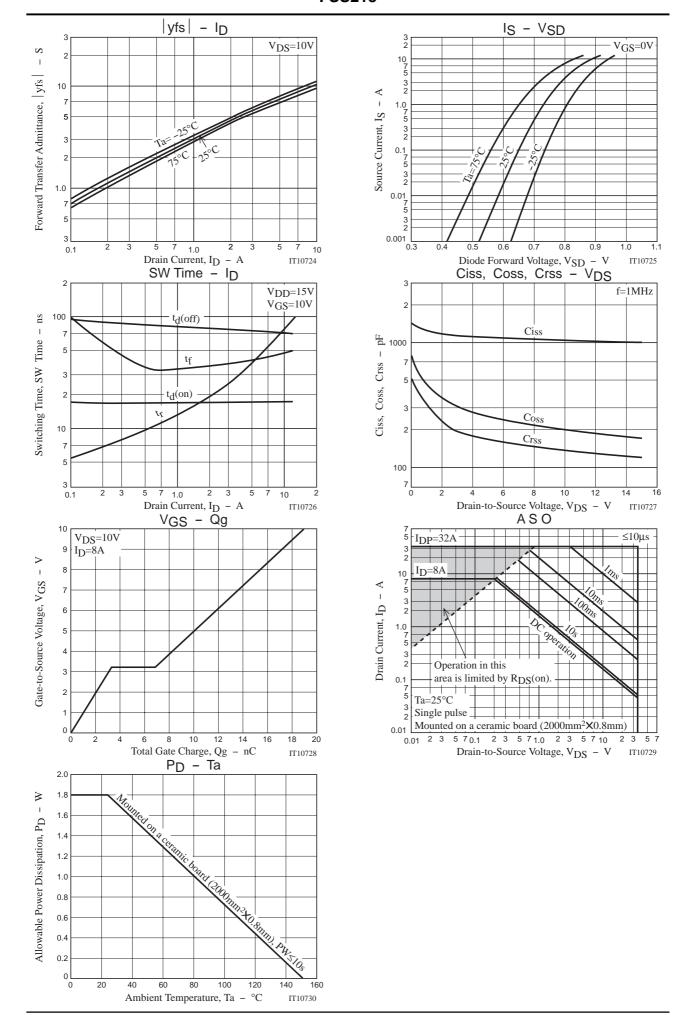


Switching Time Test Circuit









Note on usage: Since the FSS218 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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